

AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Appln. No. 09/801,695

B'
 cont
 C' a current confinement structure formed above said upper optical waveguide layer;

said upper optical waveguide layer has a first thickness smaller than a second thickness of
said lower optical waveguide layer;

~~wherein said index-guided structure has a stripe width of 4 micrometers or smaller.~~

B2C' 10 (Amended). A semiconductor laser device according to claim 9, wherein said upper
optical waveguide layer has a first thickness, and said lower optical waveguide layer has a
second thickness, and a sum of said first and second thickness is 0.5 micrometers or greater.